

Johann P Reithmaier

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#	Paper	IF	Citations
402	Strong coupling in a single quantum dot-semiconductor microcavity system. <i>Nature</i> , 2004 , 432, 197-200	50.4	1491
401	Fine structure of neutral and charged excitons in self-assembled In(Ga)As/(Al)GaAs quantum dots. <i>Physical Review B</i> , 2002 , 65,	3.3	837
400	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2017 , 23, 1-3	3.8	442
399	Electron and Hole g Factors and Exchange Interaction from Studies of the Exciton Fine Structure in In _{0.60} Ga _{0.40} As Quantum Dots. <i>Physical Review Letters</i> , 1999 , 82, 1748-1751	7.4	360
398	Optical Modes in Photonic Molecules. <i>Physical Review Letters</i> , 1998 , 81, 2582-2585	7.4	289
397	Long-wavelength InP-based quantum-dash lasers. <i>IEEE Photonics Technology Letters</i> , 2002 , 14, 735-737	2.2	133
396	Control of vertically coupled InGaAs/GaAs quantum dots with electric fields. <i>Physical Review Letters</i> , 2005 , 94, 157401	7.4	127
395	Size Dependence of Confined Optical Modes in Photonic Quantum Dots. <i>Physical Review Letters</i> , 1997 , 78, 378-381	7.4	114
394	Zeeman splitting of excitons and biexcitons in single In _{0.60} Ga _{0.40} As/GaAs self-assembled quantum dots. <i>Physical Review B</i> , 1998 , 58, R7508-R7511	3.3	114
393	Tunable photonic crystals fabricated in III-V semiconductor slab waveguides using infiltrated liquid crystals. <i>Applied Physics Letters</i> , 2003 , 82, 2767-2769	3.4	110
392	InP based lasers and optical amplifiers with wire-/dot-like active regions. <i>Journal Physics D: Applied Physics</i> , 2005 , 38, 2088-2102	3	101
391	Weak and strong coupling of photons and excitons in photonic dots. <i>Physical Review B</i> , 1998 , 57, 9950-9956	3.5	98
390	Telecom-wavelength (1.5 μ m) single-photon emission from InP-based quantum dots. <i>Applied Physics Letters</i> , 2013 , 103, 162101	3.4	87
389	Optical Demonstration of a Crystal Band Structure Formation. <i>Physical Review Letters</i> , 1999 , 83, 5374-5377	7.4	85
388	Band offset in elastically strained InGaAs/GaAs multiple quantum wells determined by optical absorption and electronic Raman scattering. <i>Applied Physics Letters</i> , 1990 , 56, 536-538	3.4	84
387	Lasing in high-Q quantum-dot micropillar cavities. <i>Applied Physics Letters</i> , 2006 , 89, 051107	3.4	82
386	Transient electromagnetically induced transparency in self-assembled quantum dots. <i>Applied Physics Letters</i> , 2008 , 92, 041113	3.4	81

385	Size control of InAs quantum dashes. <i>Applied Physics Letters</i> , 2005 , 86, 253112	3.4	74
384	Line narrowing in single semiconductor quantum dots: Toward the control of environment effects. <i>Physical Review B</i> , 2002 , 66,	3.3	73
383	Er doped nanocrystalline ZnO planar waveguide structures for 1.55 μm amplifier applications. <i>Applied Physics Letters</i> , 1999 , 75, 2005-2007	3.4	72
382	Highly efficient GaInAs/(Al)GaAs quantum-dot lasers based on a single active layer versus 980 nm high-power quantum-well lasers. <i>Applied Physics Letters</i> , 2000 , 77, 1419-1421	3.4	71
381	High-performance GaInAs/GaAs quantum-dot lasers based on a single active layer. <i>Applied Physics Letters</i> , 1999 , 74, 2915-2917	3.4	71
380	On the nature of quantum dash structures. <i>Journal of Applied Physics</i> , 2004 , 95, 6103-6111	2.5	67
379	InAs/InP Quantum-Dash Lasers and Amplifiers. <i>Proceedings of the IEEE</i> , 2007 , 95, 1779-1790	14.3	66
378	Semiconductor quantum dot microcavity pillars with high-quality factors and enlarged dot dimensions. <i>Applied Physics Letters</i> , 2005 , 86, 111105	3.4	66
377	Broad-band wavelength conversion based on cross-gain modulation and four-wave mixing in InAs-InP quantum-dash semiconductor optical amplifiers operating at 1550 nm. <i>IEEE Photonics Technology Letters</i> , 2003 , 15, 563-565	2.2	65
376	Low-threshold high-quantum-efficiency laterally gain-coupled InGaAs/AlGaAs distributed feedback lasers. <i>Applied Physics Letters</i> , 1999 , 74, 483-485	3.4	63
375	Correlation between the gain profile and the temperature-induced shift in wavelength of quantum-dot lasers. <i>Applied Physics Letters</i> , 2002 , 81, 217-219	3.4	62
374	Epitaxial growth of 1.55 μm emitting InAs quantum dashes on InP-based heterostructures by GS-MBE for long-wavelength laser applications. <i>Journal of Crystal Growth</i> , 2003 , 251, 248-252	1.6	58
373	Optical properties of Ga _{0.8} In _{0.2} As/GaAs surface quantum wells. <i>Physical Review B</i> , 1993 , 48, 14741-14744	3.5	53
372	Strong exciton-photon coupling in semiconductor quantum dot systems. <i>Semiconductor Science and Technology</i> , 2008 , 23, 123001	1.8	50
371	Investigation of the critical layer thickness in elastically strained InGaAs/GaAlAs quantum wells by photoluminescence and transmission electron microscopy. <i>Applied Physics Letters</i> , 1989 , 54, 48-50	3.4	48
370	The role of Auger recombination in InAs 1.3- μm quantum-dot lasers investigated using high hydrostatic pressure. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2003 , 9, 1300-1307	3.8	47
369	Polariton-polariton scattering in semiconductor microcavities: Experimental observation of thresholdlike density dependence. <i>Physical Review B</i> , 2000 , 61, R2409-R2412	3.3	47
368	High gain 1.55 μm diode lasers based on InAs quantum dot like active regions. <i>Applied Physics Letters</i> , 2011 , 98, 201102	3.4	46

367	Lateral coupling in material independent way to complex coupled DFB lasers. <i>Optical Materials</i> , 2001 , 17, 19-25	3-3	44
366	Enhancement of spontaneous emission rates by three-dimensional photon confinement in Bragg microcavities. <i>Physical Review B</i> , 1997 , 56, R4367-R4370	3-3	43
365	Influence of the strain on the formation of GaInAs/GaAs quantum structures. <i>Journal of Crystal Growth</i> , 2006 , 286, 6-10	1.6	42
364	. <i>IEEE Photonics Technology Letters</i> , 2001 , 13, 764-766	2.2	42
363	Bioproperties of nanocrystalline diamond/amorphous carbon composite films. <i>Diamond and Related Materials</i> , 2007 , 16, 735-739	3-5	41
362	Cell adhesion and growth on ultrananocrystalline diamond and diamond-like carbon films after different surface modifications. <i>Applied Surface Science</i> , 2014 , 297, 95-102	6-7	40
361	Edge-emitting GaInAs-AlGaAs microlasers. <i>IEEE Photonics Technology Letters</i> , 1999 , 11, 943-945	2.2	40
360	Influence of doping density on electron dynamics in GaAs/AlGaAs quantum cascade lasers. <i>Journal of Applied Physics</i> , 2006 , 99, 103106	2-5	38
359	Indium desorption during MBE growth of strained InGaAs layers. <i>Journal of Crystal Growth</i> , 1991 , 111, 407-412	1.6	38
358	Experimental evidence for the transition from two- to three-dimensional behavior of excitons in quantum-well structures. <i>Physical Review B</i> , 1991 , 43, 4933-4938	3-3	38
357	Influence of the As ₂ /As ₄ growth modes on the formation of quantum dot-like InAs islands grown on InAlGaAs/InP (100). <i>Applied Physics Letters</i> , 2010 , 96, 191903	3-4	37
356	Coherent photonic coupling of semiconductor quantum dots. <i>Optics Letters</i> , 2006 , 31, 1738-40	3	37
355	Strong variation of the exciton g factors in self-assembled In _{0.60} Ga _{0.40} As quantum dots. <i>Physical Review B</i> , 1999 , 60, R8481-R8484	3-3	35
354	Temperature stability of static and dynamic properties of 1.55 μm quantum dot lasers. <i>Optics Express</i> , 2018 , 26, 6056-6066	3-3	33
353	Single photon emission at 1.55 μm from charged and neutral exciton confined in a single quantum dash. <i>Applied Physics Letters</i> , 2014 , 105, 021909	3-4	33
352	Tribological properties of ultrananocrystalline diamond films in various test atmosphere. <i>Tribology International</i> , 2011 , 44, 2042-2049	4-9	33
351	Focused ion-beam implantation induced thermal quantum-well intermixing for monolithic optoelectronic device integration. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 1998 , 4, 595-605	3-8	33
350	Radiative emission dynamics of quantum dots in a single cavity micropillar. <i>Physical Review B</i> , 2006 , 74,	3-3	33

349	High-performance 980 nm quantum dot lasers for high-power applications. <i>Electronics Letters</i> , 2001 , 37, 353	1.1	33
348	Exciton-photon coupling in photonic wires. <i>Physical Review B</i> , 1998 , 57, R6807-R6810	3.3	33
347	Photoreflectance-probed excited states in InAs _{1-x} GaAs quantum dashes grown on InP substrate. <i>Applied Physics Letters</i> , 2006 , 89, 031908	3.4	32
346	Ultrafast gain and index dynamics of quantum dash structures emitting at 1.55 μ m. <i>Applied Physics Letters</i> , 2006 , 89, 081102	3.4	32
345	High-temperature properties of GaInAs/AlGaAs lasers with improved carrier confinement by short-period superlattice quantum well barriers. <i>Applied Physics Letters</i> , 1998 , 73, 2863-2865	3.4	32
344	Optical gain properties of InAs _{1-x} AlGaAs _x InP quantum dash structures with a spectral gain bandwidth of more than 300nm. <i>Applied Physics Letters</i> , 2006 , 89, 061107	3.4	30
343	High Speed 1.55 μ m InAs/InGaAlAs/InP Quantum Dot Lasers. <i>IEEE Photonics Technology Letters</i> , 2014 , 26, 11-13	2.2	29
342	Multiple wavelength amplification in wide band high power 1550 nm quantum dash optical amplifier. <i>Electronics Letters</i> , 2004 , 40, 760	1.1	29
341	InAs _{1-x} InP 1550 nm quantum dash semiconductor optical amplifiers. <i>Electronics Letters</i> , 2002 , 38, 1350	1.1	29
340	Laser emission from photonic dots. <i>Applied Physics Letters</i> , 1997 , 71, 488-490	3.4	28
339	Optically probed wetting layer in InAs/InGaAlAs/InP quantum-dash structures. <i>Applied Physics Letters</i> , 2005 , 86, 101904	3.4	28
338	Optical spectroscopy of single InAs/InGaAs quantum dots in a quantum well. <i>Applied Physics Letters</i> , 2002 , 81, 4898-4900	3.4	28
337	High-density 1.54 μ m InAs/InGaAlAs/InP(100) based quantum dots with reduced size inhomogeneity. <i>Journal of Crystal Growth</i> , 2015 , 425, 299-302	1.6	27
336	Magneto-optical investigations of single self-assembled InAs/InGaAlAs quantum dashes. <i>Applied Physics Letters</i> , 2003 , 82, 2799-2801	3.4	27
335	Gain and noise saturation of wide-band InAs-InP quantum dash optical amplifiers: model and experiments. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2005 , 11, 1015-1026	3.8	27
334	Exciton and biexciton dynamics in single self-assembled InAs/InGaAlAs/InP quantum dash emitting near 1.55 μ m. <i>Applied Physics Letters</i> , 2013 , 103, 253113	3.4	26
333	Enhanced direct-modulated bandwidth of 37 GHz by a multi-section laser with a coupled-cavity-injection-grating design. <i>Electronics Letters</i> , 2003 , 39, 1592	1.1	26
332	High-power quantum dot lasers with improved temperature stability of emission wavelength for uncooled pump sources. <i>Electronics Letters</i> , 2005 , 41, 1125	1.1	26

331	Single-photon emission of InAs/InP quantum dashes at 1.55 μm and temperatures up to 80 K. <i>Applied Physics Letters</i> , 2016 , 108, 163108	3-4	26
330	Telecom wavelength single quantum dots with very small excitonic fine-structure splitting. <i>Applied Physics Letters</i> , 2018 , 112, 172102	3-4	25
329	Electronic structure, morphology and emission polarization of enhanced symmetry InAs quantum-dot-like structures grown on InP substrates by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2013 , 114, 094306	2-5	25
328	Rabi oscillations and self-induced transparency in InAs/InP quantum dot semiconductor optical amplifier operating at room temperature. <i>Optics Express</i> , 2013 , 21, 26786-96	3-3	25
327	Influence of electronic coupling on the radiative lifetime in the (In,Ga)As/GaAs quantum dot quantum well system. <i>Physical Review B</i> , 2012 , 85,	3-3	25
326	Photoreflectance spectroscopy of vertically coupled InGaAs/GaAs double quantum dots. <i>Solid State Communications</i> , 2001 , 117, 401-406	1-6	25
325	Large linewidth reduction in semiconductor lasers based on atom-like gain material. <i>Optica</i> , 2019 , 6, 1071	8-6	25
324	Heterodyne pump probe measurements of nonlinear dynamics in an indium phosphide photonic crystal cavity. <i>Applied Physics Letters</i> , 2013 , 103, 181120	3-4	24
323	Wettability and protein adsorption on ultrananocrystalline diamond/amorphous carbon composite films. <i>Diamond and Related Materials</i> , 2009 , 18, 895-898	3-5	23
322	Improved performance of MBE grown quantum-dot lasers with asymmetric dots in a well design emitting near 1.3 μm . <i>Journal of Crystal Growth</i> , 2003 , 251, 742-747	1-6	23
321	Importance of Auger recombination in InAs 1.3 μm quantum dot lasers. <i>Electronics Letters</i> , 2003 , 39, 58	1-1	23
320	High-power 980 nm quantum dot broad area lasers. <i>Electronics Letters</i> , 2003 , 39, 1655	1-1	23
319	Cross-gain modulation in inhomogeneously broadened gain spectra of InP-Based 1550 nm quantum dash optical amplifiers: Small-signal bandwidth dependence on wavelength detuning. <i>Applied Physics Letters</i> , 2003 , 82, 4660-4662	3-4	23
318	Reduction of the threshold current density of GaAs/AlGaAs quantum cascade lasers by optimized injector doping and growth conditions. <i>Journal of Crystal Growth</i> , 2005 , 278, 775-779	1-6	23
317	High-Power Tunnel-Injection 1060-nm InGaAs/AlGaAs Quantum-Dot Lasers. <i>IEEE Photonics Technology Letters</i> , 2009 , 21, 999-1001	2-2	22
316	Minimum feature sizes and ion beam profile for a focused ion beam system with post-objective lens retarding and acceleration mode. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1994 , 12, 3518		22
315	Incorporation and study of SiV centers in diamond nanopillars. <i>Diamond and Related Materials</i> , 2016 , 64, 64-69	3-5	21
314	High-Speed Low-Noise InAs/InAlGaAs/InP 1.55- μm Quantum-Dot Lasers. <i>IEEE Photonics Technology Letters</i> , 2012 , 24, 809-811	2-2	21

313	Low temperature growth of nanocrystalline and ultrananocrystalline diamond films: A comparison. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 1664-1674	1.6	21
312	Thermal quenching of photoluminescence from InAs _{1-x} Ga _{0.23} Al _{0.24} As _{1-x} P quantum dashes with different sizes. <i>Applied Physics Letters</i> , 2006 , 89, 151902	3.4	21
311	Optical properties of low-strained In _x Ga _{1-x} As _{1-x} GaAs quantum dot structures at the two-dimensional \rightarrow three-dimensional growth transition. <i>Journal of Applied Physics</i> , 2006 , 100, 013503	2.5	21
310	Deeply etched two-dimensional photonic crystals fabricated on GaAs/AlGaAs slab waveguides by using chemically assisted ion beam etching. <i>Microelectronic Engineering</i> , 2002 , 61-62, 875-880	2.5	21
309	Confinement of light hole valence-band states in pseudomorphic InGaAs/Ga(Al)As quantum wells. <i>Applied Physics Letters</i> , 1990 , 57, 957-959	3.4	21
308	Magnetic field control of the neutral and charged exciton fine structure in single quantum dashes emitting at 1.55 μm . <i>Applied Physics Letters</i> , 2015 , 106, 053114	3.4	20
307	Temperature-Insensitive High-Speed Directly Modulated 1.55- μm Quantum Dot Lasers. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 2451-2454	2.2	20
306	High-gain wavelength-stabilized 1.55 μm InAs/InP(100) based lasers with reduced number of quantum dot active layers. <i>Applied Physics Letters</i> , 2013 , 102, 221117	3.4	20
305	Plasma amination of ultrananocrystalline diamond/amorphous carbon composite films for the attachment of biomolecules. <i>Diamond and Related Materials</i> , 2011 , 20, 254-258	3.5	20
304	Complex (As ₂ S ₃) _(100-x) (AgI) _x chalcogenide glasses for gas sensors. <i>Sensors and Actuators B: Chemical</i> , 2009 , 143, 395-399	8.5	20
303	InAs/GaInAs quantum dot DFB lasers emitting at 1.3 μm . <i>Electronics Letters</i> , 2001 , 37, 634	1.1	20
302	Wide range tunable laterally coupled distributed-feedback lasers based on InGaAs-GaAs quantum dots. <i>IEEE Photonics Technology Letters</i> , 2002 , 14, 1246-1248	2.2	20
301	High frequency characteristics of InAs/GaInAs quantum dot distributed feedback lasers emitting at 1.3 μm . <i>Electronics Letters</i> , 2001 , 37, 1223	1.1	20
300	Dynamics of carrier-capture processes in Ga _x In _{1-x} As/GaAs near-surface quantum wells. <i>Physical Review B</i> , 1995 , 51, 4657-4660	3.3	20
299	Telecom wavelength emitting single quantum dots coupled to InP-based photonic crystal microcavities. <i>Applied Physics Letters</i> , 2017 , 110, 031101	3.4	19
298	Rabi oscillations in a room-temperature quantum dash semiconductor optical amplifier. <i>Physical Review B</i> , 2014 , 90,	3.3	19
297	Electron and hole g factors in InAs/InAlGaAs self-assembled quantum dots emitting at telecom wavelengths. <i>Physical Review B</i> , 2015 , 92,	3.3	19
296	Photoreflectance determination of the wetting layer thickness in the In _x Ga _{1-x} As _{1-x} GaAs quantum dot system for a broad indium content range of 0.3 μm . <i>Journal of Applied Physics</i> , 2006 , 100, 103529	2.5	19

295	22-GHz modulation bandwidth of long cavity DBR laser by using a weakly laterally coupled grating fabricated by focused ion beam lithography. <i>IEEE Photonics Technology Letters</i> , 2004 , 16, 18-20	2.2	19
294	InP-based quantum dash lasers for wide gain bandwidth applications. <i>Journal of Crystal Growth</i> , 2005 , 278, 346-350	1.6	19
293	Widely tunable narrow-linewidth 1.5 μm light source based on a monolithically integrated quantum dot laser array. <i>Applied Physics Letters</i> , 2017 , 110, 181103	3.4	18
292	Patterning of the surface termination of ultrananocrystalline diamond films for guided cell attachment and growth. <i>Surface and Coatings Technology</i> , 2017 , 321, 229-235	4.4	18
291	Exciton lifetime and emission polarization dispersion in strongly in-plane asymmetric nanostructures. <i>Physical Review B</i> , 2017 , 96,	3.3	18
290	Phonon-assisted radiative recombination of excitons confined in strongly anisotropic nanostructures. <i>Physical Review B</i> , 2014 , 90,	3.3	18
289	All-optical signal processing at 10 GHz using a photonic crystal molecule. <i>Applied Physics Letters</i> , 2013 , 103, 193510	3.4	18
288	On the development of the morphology of ultrananocrystalline diamond films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011 , 208, 70-80	1.6	18
287	Electrical properties of ultrananocrystalline diamond/amorphous carbon nanocomposite films. <i>Diamond and Related Materials</i> , 2010 , 19, 449-452	3.5	18
286	Recombination mechanisms in InAs/InP quantum dash lasers studied using high hydrostatic pressure. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, 3427-3431	1.3	18
285	Single-mode distributed feedback and microlasers based on quantum-dot gain material. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2002 , 8, 1035-1044	3.8	18
284	Recent advances in semiconductor quantum-dot lasers. <i>Comptes Rendus Physique</i> , 2003 , 4, 611-619	1.4	18
283	Gallium desorption during growth of (Al,Ga)As by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1992 , 61, 1222-1224	3.4	18
282	Large anisotropy of electron and hole g factors in infrared-emitting InAs/InAlGaAs self-assembled quantum dots. <i>Physical Review B</i> , 2016 , 93,	3.3	17
281	Polarization-dependent optical properties of planar photonic crystals infiltrated with liquid crystals. <i>Applied Physics Letters</i> , 2005 , 87, 121105	3.4	17
280	High Performance 1.3 μm Quantum-Dot Lasers. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, 1158-1161	1.4	17
279	Excitonic fine structure and binding energies of excitonic complexes in single InAs quantum dashes. <i>Physical Review B</i> , 2016 , 94,	3.3	16
278	Low-density InP-based quantum dots emitting around the 1.5 μm telecom wavelength range. <i>Applied Physics Letters</i> , 2014 , 104, 022113	3.4	16

277	Influence of the surface termination of ultrananocrystalline diamond/amorphous carbon composite films on their interaction with neurons. <i>Diamond and Related Materials</i> , 2012 , 26, 60-65	3.5	16
276	Tribological properties of nanocrystalline diamond films deposited by hot filament chemical vapor deposition. <i>AIP Advances</i> , 2012 , 2, 032164	1.5	16
275	Nanocrystalline diamond/amorphous carbon composite coatings for biomedical applications. <i>Diamond and Related Materials</i> , 2008 , 17, 882-887	3.5	16
274	Cross talk free multi channel processing of 10 Gbit/s data via four wave mixing in a 1550 nm InAs/InP quantum dash amplifier. <i>Optics Express</i> , 2008 , 16, 19072-7	3.3	16
273	Widely tunable single-mode quantum cascade lasers with two monolithically coupled Fabry-Pérot cavities. <i>Applied Physics Letters</i> , 2006 , 89, 241126	3.4	16
272	Dependence of saturation effects on electron confinement and injector doping in GaAs/Al _{0.45} Ga _{0.55} As quantum-cascade lasers. <i>Applied Physics Letters</i> , 2006 , 88, 251109	3.4	16
271	Gain, index variation, and linewidth-enhancement factor in 980-nm quantum-well and quantum-dot lasers. <i>IEEE Journal of Quantum Electronics</i> , 2005 , 41, 117-126	2	16
270	Static and dynamic properties of laterally coupled DFB lasers based on InAs/InP QDash structures. <i>Electronics Letters</i> , 2005 , 41, 808	1.1	16
269	Time-resolved chirp in an InAs/InP quantum-dash optical amplifier operating with 10Gbit/s data. <i>Applied Physics Letters</i> , 2005 , 87, 021104	3.4	16
268	High-frequency properties of 1.55 μ m laterally complex coupled distributed feedback lasers fabricated by focused-ion-beam lithography. <i>Applied Physics Letters</i> , 2000 , 77, 325-327	3.4	16
267	Short-cavity edge-emitting lasers with deeply etched distributed Bragg mirrors. <i>Electronics Letters</i> , 1999 , 35, 154	1.1	16
266	1.55 μ m single mode lasers with complex coupled distributed feedback gratings fabricated by focused ion beam implantation. <i>Applied Physics Letters</i> , 1999 , 75, 1491-1493	3.4	16
265	InGaAs/AlGaAs quantum dot DFB lasers operating up to 213°C. <i>Electronics Letters</i> , 1999 , 35, 2036	1.1	16
264	High-Purity Triggered Single-Photon Emission from Symmetric Single InAs/InP Quantum Dots around the Telecom C-Band Window. <i>Advanced Quantum Technologies</i> , 2020 , 3, 1900082	4.3	16
263	Nanocrystalline diamond containing hydrogels and coatings for acceleration of osteogenesis. <i>Diamond and Related Materials</i> , 2011 , 20, 165-169	3.5	15
262	A nearly instantaneous gain response in quantum dash based optical amplifiers. <i>Applied Physics Letters</i> , 2010 , 97, 131108	3.4	15
261	Microthermography of diode lasers: The impact of light propagation on image formation. <i>Journal of Applied Physics</i> , 2009 , 105, 014502	2.5	15
260	Influence of the nucleation density on the structure and mechanical properties of ultrananocrystalline diamond films. <i>Diamond and Related Materials</i> , 2009 , 18, 151-154	3.5	15

259	Enhanced exciton-phonon scattering in In _x Ga _{1-x} As/GaAs quantum wires. <i>Physical Review B</i> , 1997 , 56, 12096-12099	3.3	15
258	GaInAs/(Al)GaAs quantum-dot lasers with high wavelength stability. <i>Semiconductor Science and Technology</i> , 2008 , 23, 085022	1.8	15
257	On the tunnel injection of excitons and free carriers from In _{0.53} Ga _{0.47} As/In _{0.53} Ga _{0.23} Al _{0.24} As quantum well to InAs/In _{0.53} Ga _{0.23} Al _{0.24} As quantum dashes. <i>Applied Physics Letters</i> , 2006 , 89, 061902	3.4	15
256	High brightness GaInAs/(Al)GaAs quantum-dot tapered lasers at 980 nm with high wavelength stability. <i>Applied Physics Letters</i> , 2004 , 84, 2238-2240	3.4	15
255	12 [micro sign]m long edge-emitting quantum-dot laser. <i>Electronics Letters</i> , 2001 , 37, 690	1.1	15
254	Highly Resolved Maskless Patterning on InP by Focused Ion Beam Enhanced Wet Chemical Etching. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, 6142-6144	1.4	15
253	First order gain-coupled GaInAs/GaAs distributed feedback laser diodes patterned by focused ion beam implantation. <i>Applied Physics Letters</i> , 1996 , 69, 1906-1908	3.4	15
252	Coherent control in a semiconductor optical amplifier operating at room temperature. <i>Nature Communications</i> , 2014 , 5, 5025	17.4	14
251	Site-controlled InAs quantum dots grown on a 55 nm thick GaAs buffer layer. <i>Applied Physics Letters</i> , 2009 , 95, 243106	3.4	14
250	Characterization of pulsed laser deposited chalcogenide thin layers. <i>Applied Surface Science</i> , 2009 , 255, 5318-5321	6.7	14
249	Investigation of the UV/O ₃ treatment of ultrananocrystalline diamond films. <i>Surface and Interface Analysis</i> , 2010 , 42, 1152-1155	1.5	14
248	1.54 [micro sign]m singlemode InP-based Q-dash lasers. <i>Electronics Letters</i> , 2003 , 39, 985	1.1	14
247	Device performance and wavelength tuning behavior of ultra-short quantum-cascade microlasers with deeply etched Bragg-mirrors. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2005 , 11, 1048-1054	3.8	14
246	Photonic defect states in chains of coupled microresonators. <i>Physical Review B</i> , 2001 , 64,	3.3	14
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